
ECE 428 Programmable ASIC Design

Programming Technologies

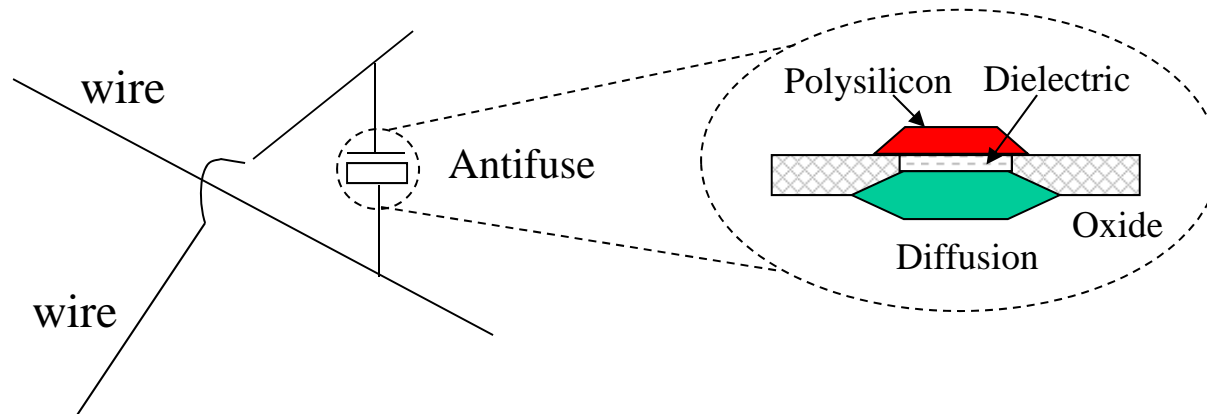
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Programming Techniques in Configurable ICs

- ☐ Poly-Diffusion Antifuse
- ☐ Metal-Metal Antifuse
- ☐ SRAM-Based Programming Technique
- ☐ EPROM-based Programming Technique
- ☐ EEPROM-based Programming Technique

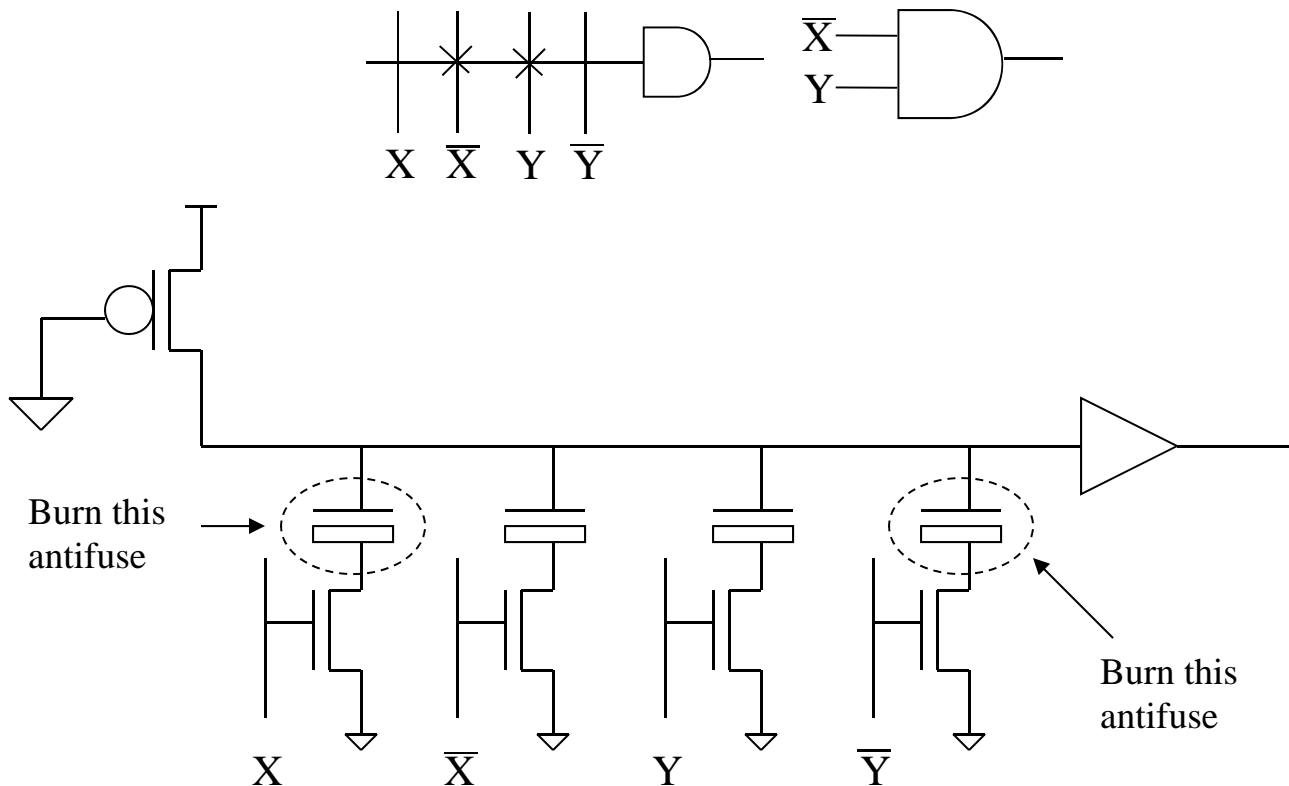
Poly-Diffusion Antifuse

- ❑ An *antifuse* is the opposite of a regular fuse. It is an open path until a programming current is forced through it by applying a high programming voltage across it.
- ❑ Advantage: small (allow denser switch population).
- ❑ Disadvantage: only one-time programmable.



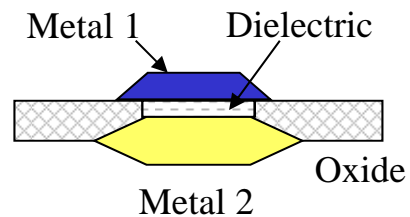
Example: Antifuse Techniques in PAL & PLA

□ Implementation of wired-AND gate

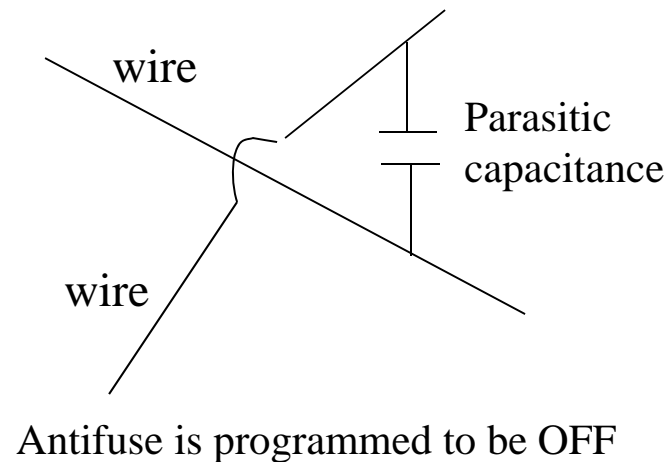
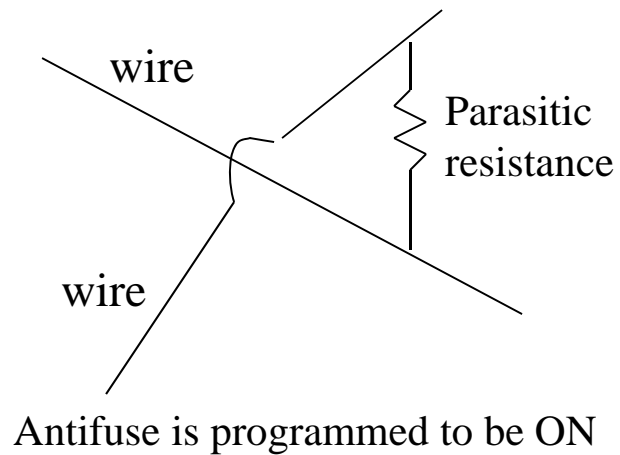


Metal-Metal Antifuse

❑ Cross section of a metal-metal antifuse

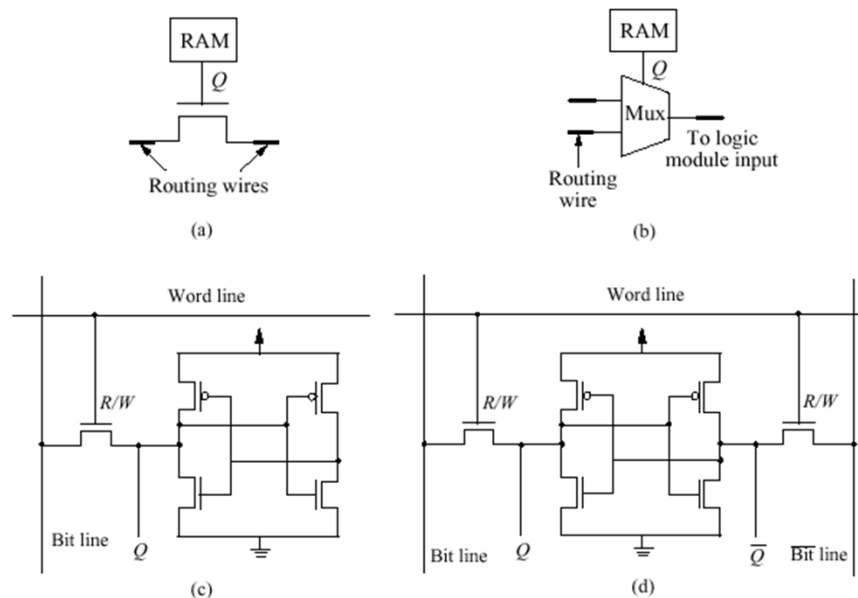


❑ Parasitic effects of antifuse

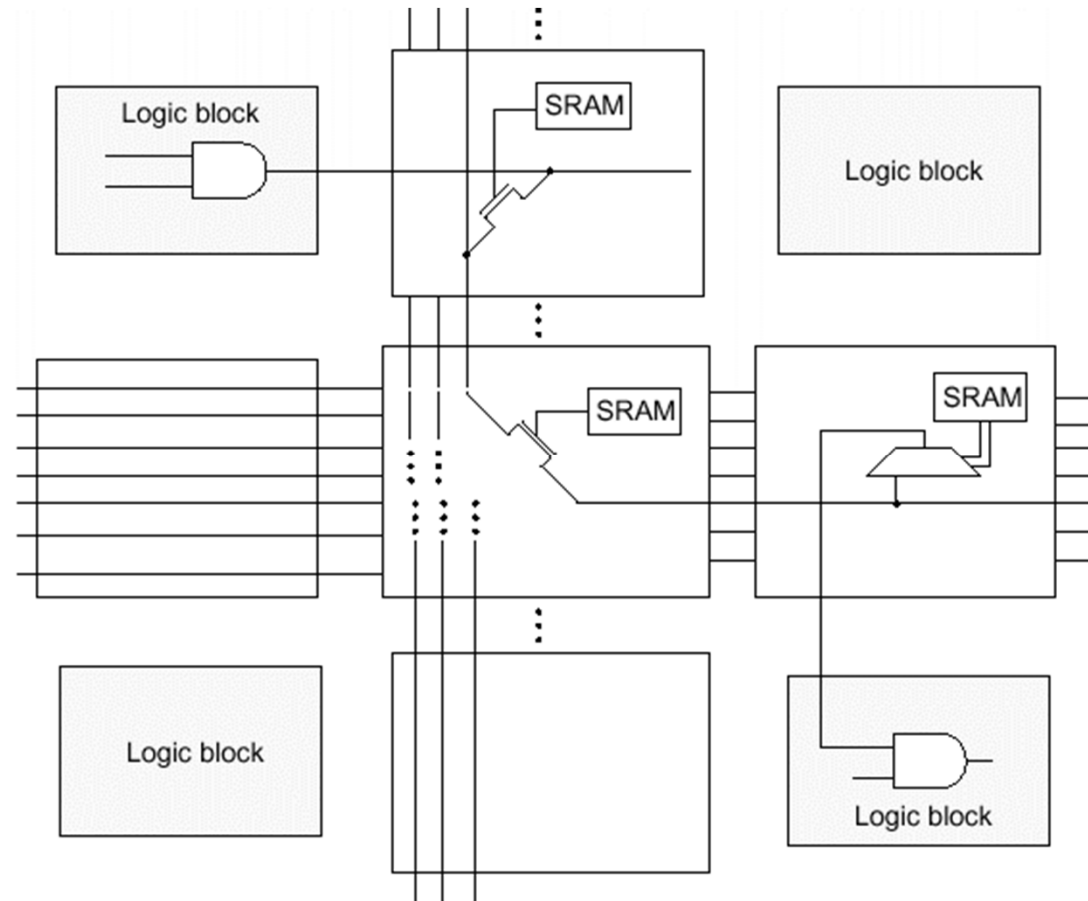


SRAM-Based Programming technique

- ❑ Use SRAM cells to control pass transistors or multiplexers by the bit-content in the SRAM cells.
- ❑ Advantage: re-programmable.
- ❑ Disadvantage: occupy more space.

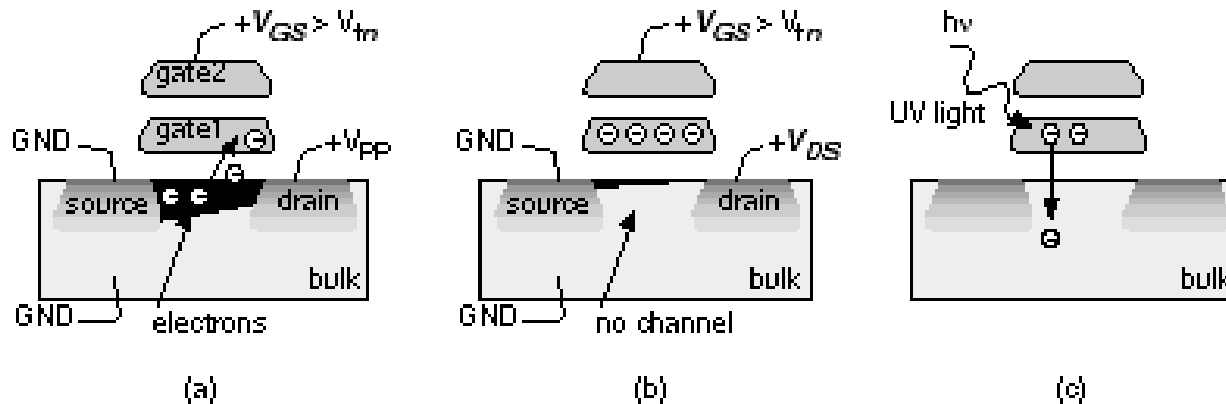


Example: SRAM-Controlled Programmable Switch



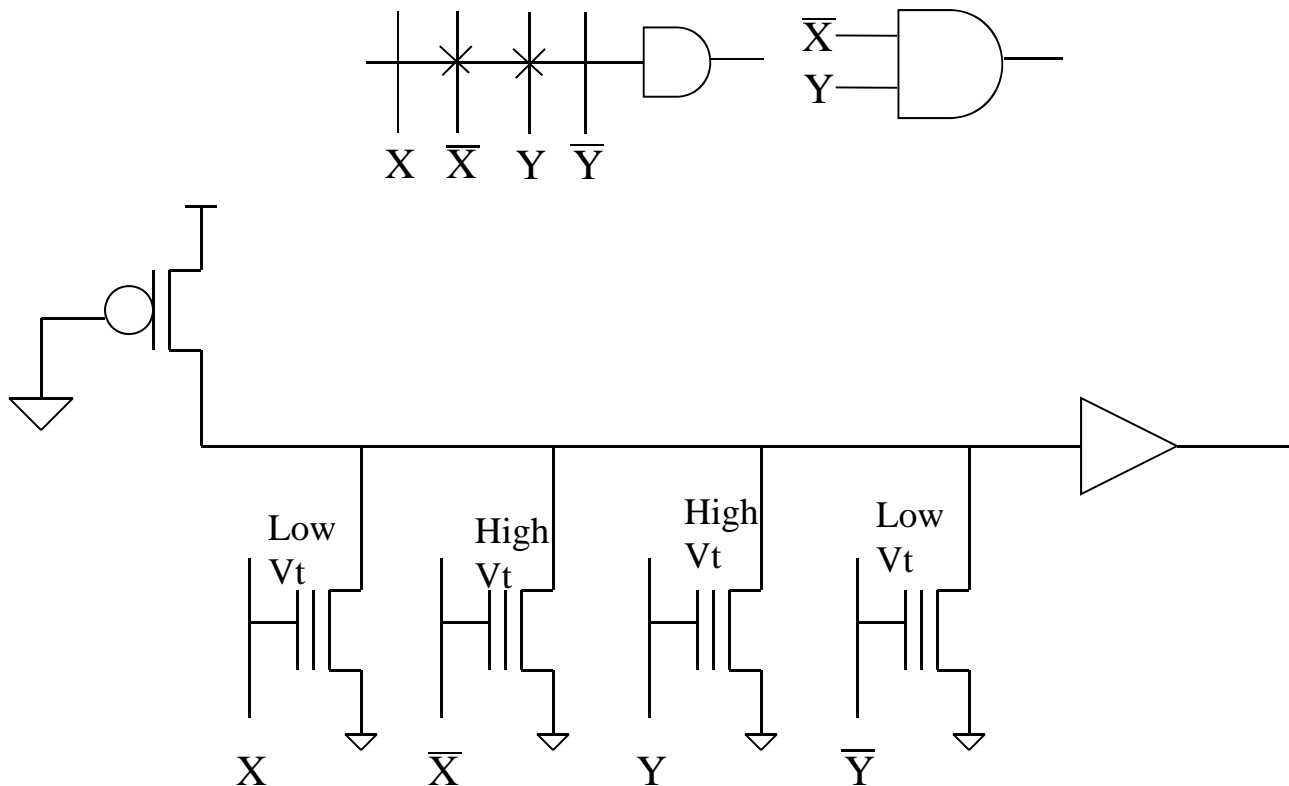
EPROM & EEPROM Programming technique

- ❑ An EPROM (r EEPROM) cell looks like a normal MOS transistor except that it has a second, floating, gate.
- ❑ To program an EPROM (or EEPROM) cell, apply a high voltage to the drain of the transistor. It results in electrons trapped in the floating gate and consequently increasing the threshold voltage.
- ❑ To erase an EPROM cell, expose the chip to UV light.
- ❑ To erase an EEPROM cell, electrical field is used to remove electrons from the floating gate.



EPROM & EEPROM Programming technique

□ Implementation of wired-AND gate



Comparison of Different Programming Techniques

Programming technology	SRAM	Poly-Diffusion antifuse	Metal-Meta antifuse	EPROM	EEPROM
Manufacturing Complexity	+	-	-	-	-
Re-programmable?	Yes In circuit	No	No	Yes Out of circuit	Yes In circuit
Physical size	Large (12X)	Small (2X)	Small (1X)	Small	Small
ON resistance (Ω)	600–800	100–500	30–80	1-4K	1-4K
OFF capacitance (fF)	10–50	3–5	1	10–50	10–50
Power consumption	++	+	+	-	-
Volatile?	Yes	No	No	No	No

+ Desirable; - no desirable